MOSFETs Silicon N-channel MOS (U-MOSⅧ-H)

TK32A12N1

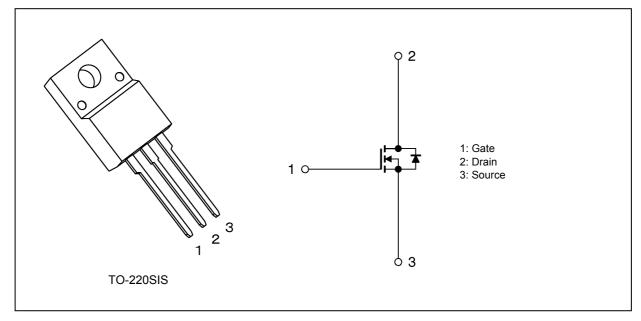
1. Applications

• Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)}$ = 11.0 m Ω (typ.) (V_{GS} = 10 V)
- (2) Low leakage current: $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 120 \ V)$
- (3) Enhancement mode: V_{th} = 2.0 to 4.0 V (V_{DS} = 10 V, I_D = 0.5 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25^{\circ}C$ unless otherwise specified)

| Characteristi | Symbol | Rating | Unit | | |
|-------------------------------|-------------------------|--------------------|------------------|------------|----|
| Drain-source voltage | | | V _{DSS} | 120 | V |
| Gate-source voltage | | | V _{GSS} | ±20 | |
| Drain current (DC) | (Silicon limit) | (Note 1), (Note 2) | I _D | 60 | A |
| Drain current (DC) | (T _c = 25°C) | (Note 1) | Ι _D | 32 | |
| Drain current (pulsed) | (t = 1 ms) | (Note 1) | I _{DP} | 110 | |
| Power dissipation | (T _c = 25°C) | | PD | 30 | W |
| Single-pulse avalanche energy | | (Note 3) | E _{AS} | 48 | mJ |
| Avalanche current | | | I _{AR} | 32 | A |
| Channel temperature | | | T _{ch} | 150 | °C |
| Storage temperature | | | T _{stg} | -55 to 150 | |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production 2013-02

5. Thermal Characteristics

| Characteristics | Symbol | Max | Unit |
|---------------------------------------|-----------------------|------|------|
| Channel-to-case thermal resistance | R _{th(ch-c)} | 4.16 | °C/W |
| Channel-to-ambient thermal resistance | R _{th(ch-a)} | 62.5 | |

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Limited by silicon chip capability.

Note 3: V_{DD} = 80 V, T_{ch} = 25°C (initial), L = 46.1 μ H, I_{AR} = 32 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

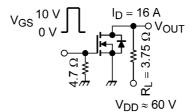
6.1. Static Characteristics (Ta = 25°C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|----------------------|---|-----|------|------|------|
| Gate leakage current | I _{GSS} | V_{GS} = ±20 V, V_{DS} = 0 V | _ | _ | ±0.1 | μA |
| Drain cut-off current | I _{DSS} | V _{DS} = 120 V, V _{GS} = 0 V | _ | — | 10 | |
| Drain-source breakdown voltage | V _{(BR)DSS} | I _D = 10 mA, V _{GS} = 0 V | 120 | | _ | V |
| Drain-source breakdown voltage (Note 4) | V _{(BR)DSX} | I _D = 10 mA, V _{GS} = -20 V | 90 | _ | _ | |
| Gate threshold voltage | V _{th} | V _{DS} = 10 V, I _D = 0.5 mA | 2.0 | — | 4.0 | |
| Drain-source on-resistance | R _{DS(ON)} | V _{GS} = 10 V, I _D = 16 A | | 11.0 | 13.8 | mΩ |

Note 4: If a reverse bias is applied between gate and source, this device enters V_{(BR)DSX} mode. Note that the drainsource breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|------------------|--|-----|------|-----|------|
| Input capacitance | C _{iss} | V _{DS} = 60 V, V _{GS} = 0 V, f = 1 MHz | _ | 2000 | — | pF |
| Reverse transfer capacitance | C _{rss} | | _ | 13 | — | |
| Output capacitance | C _{oss} | | _ | 330 | — | |
| Gate resistance | r _g | _ | _ | 1.9 | — | Ω |
| Switching time (rise time) | tr | See Figure 6.2.1 | _ | 14 | — | ns |
| Switching time (turn-on time) | t _{on} | | _ | 33 | — | |
| Switching time (fall time) | t _f | | _ | 14 | — | |
| Switching time (turn-off time) | t _{off} | | _ | 43 | _ | |



 $Duty \le 1\%, \ t_W = 10 \ \mu s$ Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

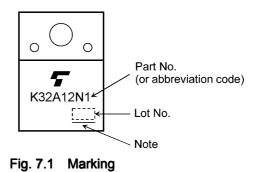
| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|------------------|--|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg | $V_{DD} \approx 96$ V, V_{GS} = 10 V, I_D = 32 A | — | 34 | — | nC |
| Gate-source charge 1 | Q _{gs1} | | _ | 13 | _ | |
| Gate-drain charge | Q _{gd} | | _ | 9.8 | _ | |
| Gate switch charge | Q _{SW} | | | 15 | | |

6.4. Source-Drain Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

| Characteristics | | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|----------|------------------|---|-----|------|------|------|
| Reverse drain current (DC) | (Note 5) | I _{DR} | — | _ | _ | 32 | А |
| Reverse drain current (pulsed) | (Note 5) | I _{DRP} | — | _ | — | 110 | |
| Diode forward voltage | | V _{DSF} | I_{DR} = 32 A, V_{GS} = 0 V | _ | — | -1.2 | V |
| Reverse recovery time | (Note 6) | t _{rr} | I _{DR} = 32 A, V _{GS} = 0 V | _ | 73 | _ | ns |
| Reverse recovery charge | (Note 6) | Q _{rr} | -dI _{DR} /dt = 100 A/µs | | 160 | | nC |

Note 5: Ensure that the channel temperature does not exceed 150°C. Note 6: Ensure that V_{DS} peak does not exceed V_{DSS} .

7. Marking (Note)



Note: A line under a Lot No. identifies the indication of product Labels.

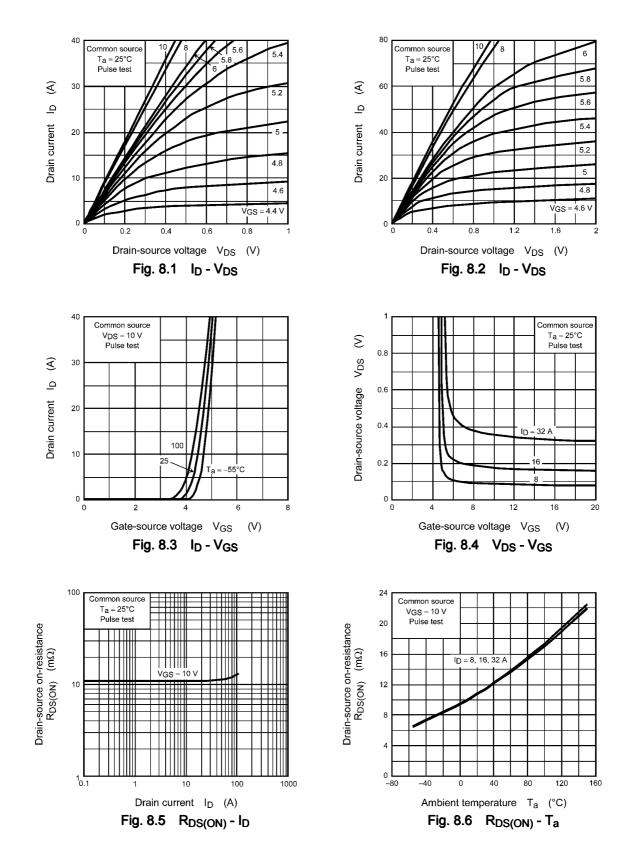
Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

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The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

8. Characteristics Curves (Note)



5

3

2

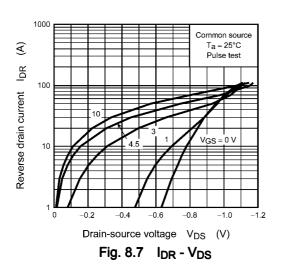
0 L -80

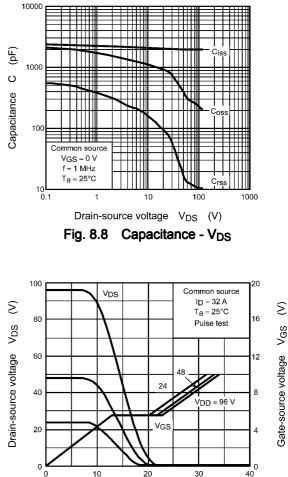
-40

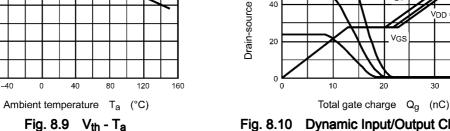
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S

Gate threshold voltage Vth





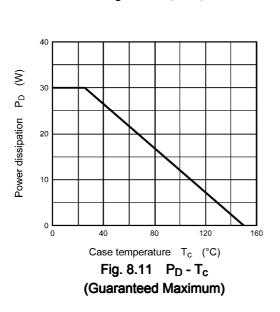


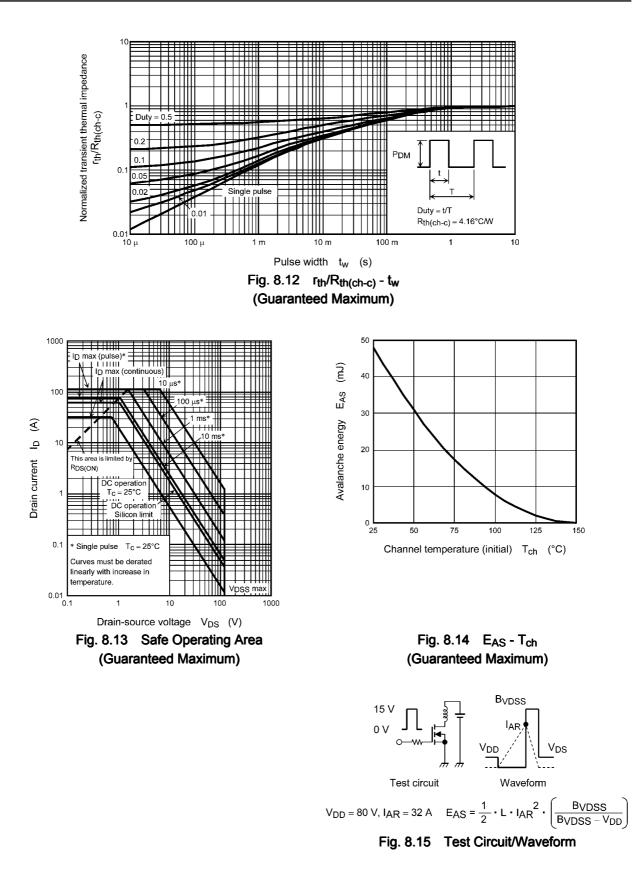
Common source

VDS = 10 V ID = 0.5 mA

Pulse test

Fig. 8.10 Dynamic Input/Output Characteristics



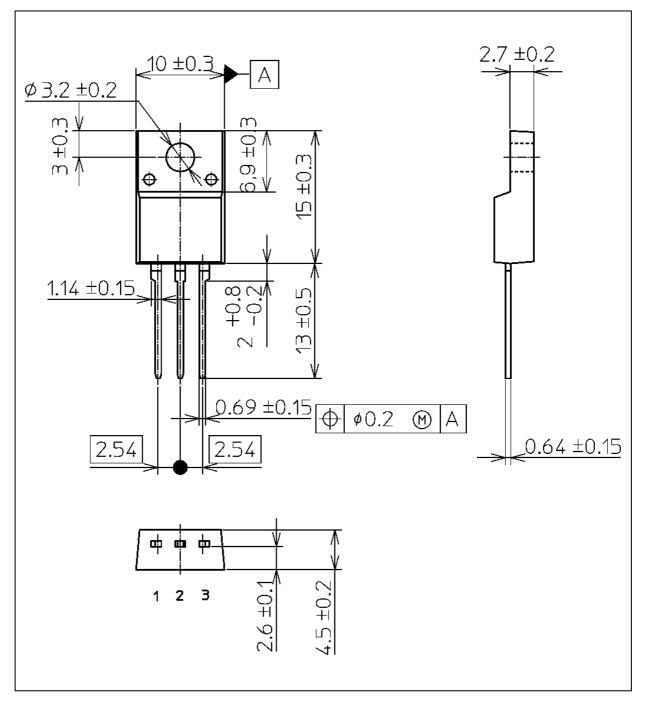


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

TK32A12N1

Unit: mm



Weight: 1.7 g (typ.)

| Package Name(s) | |
|---------------------|--|
| JEITA: SC-67 | |
| TOSHIBA: 2-10U1S | |
| Nickname: TO-220SIS | |

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